Preferred Device

Sensitive Gate Triacs

Silicon Bidirectional Thyristors

Designed primarily for industrial and consumer applications for full–wave control of AC loads such as appliance controls, heater controls, motor controls, and other power switching applications.

Features

- Sensitive Gate Triggering in 3 Modes for AC Triggering on Sinking Current Sources
- Four Mode Triggering for Drive Circuits that Source Current
- All Diffused and Glass–Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance and High Heat Dissipation
- Center Gate Geometry for Uniform Current Spreading
- Pb–Free Packages are Available*



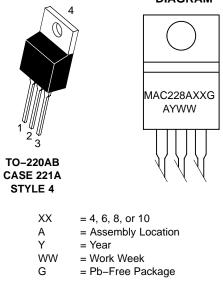
ON Semiconductor®

http://onsemi.com

TRIACS 8 AMPERES RMS 200 – 800 VOLTS







ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Value	Unit	
Peak Repetitive Off–State Voltage [,] (Note 1) (T _J = -40 to 110°C, Sine Wave, 50 to 60 Hz, Gate Open)	MAC228A4 MAC228A6 MAC228A8 MAC228A10	Vdrm, Vrrm	200 400 600 800	V
On-State RMS Current, (T _C = 80°C) – Full Cycle Sine Wave 50 to 60 Hz			8.0	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _J = 110°C)		ITSM	80	A
Circuit Fusing Considerations, (t = 8.3 ms)	l ² t	26	A ² s	
Peak Gate Current, (t $\leq 2 \mu s$, T _C = 80°C)		I _{GM}	±2.0	А
Peak Gate Voltage, (t $\leq 2 \ \mu s$, T _C = 80°C)		V _{GM}	±10	V
Peak Gate Power, (t \leq 2 µs, T _C = 80°C)	P _{GM}	20	W	
Average Gate Power, (t \leq 8.3 ms, T _C = 80°C)	P _{G(AV)}	0.5	W	
Operating Junction Temperature Range		TJ	-40 to 110	°C
Storage Temperature Range		T _{stg}	-40 to 150	°C
Mounting Torque		-	8.0	in lb

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

THERMAL CHARACTERISTICS

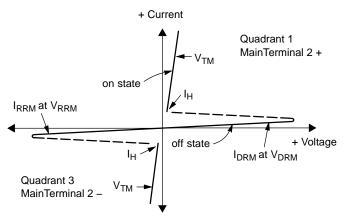
Characteristic	Symbol	Value	Unit
Thermal Resistance – Junction-to-Case	$R_{\theta JC}$	2.0	°C/W
Thermal Resistance – Junction-to-Ambient	R_{\thetaJA}	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	ΤL	260	°C

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

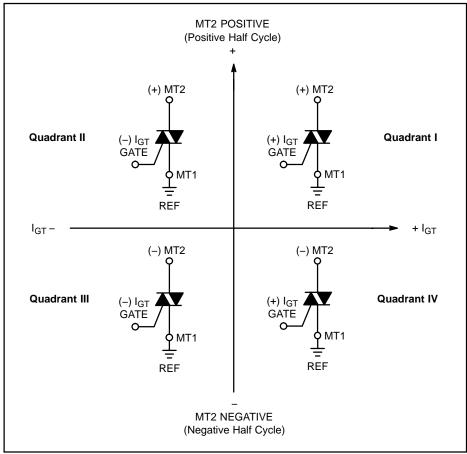
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Peak Repetitive Blocking Current, (V _D = Rated V _{DRM} , V _{RRM} ; Gate Open) T _J = 25°C T _J = 110°C	I _{DRM} , I _{RRM}			10 2.0	μA mA
ON CHARACTERISTICS					
Peak On-State Voltage, (I _{TM} = \pm 11 A Peak, Pulse Width \leq 2 ms, Duty Cycle \leq 2%)	V _{TM}	-	-	1.8	V
Gate Trigger Current (Continuous DC), (V _D = 12 V, R _L = 100 Ω) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+)	I _{GT}			5.0 10	mA
Gate Trigger Voltage (Continuous DC), (V _D = 12 V, R _L = 100 Ω) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+)	V _{GT}			2.0 2.5	V
Gate Non–Trigger Voltage (Continuous DC), (V _D = 12 V, T _C = 110°C, R _L = 100 Ω) All Four Quadrants	V _{GD}	0.2	-	-	V
Holding Current, (V _D = 12 Vdc, Initiating Current = \pm 200 mA, Gate Open)	Ι _Η	-	_	15	mA
Gate–Controlled Turn–On Time, (V_D = Rated V_{DRM} , I_{TM} = 16 A Peak, I_G = 30 mA)	t _{gt}	-	1.5	-	μs
DYNAMIC CHARACTERISTICS	-				
Critical Rate of Rise of Off-State Voltage, (V_D = Rated V_{DRM} , Exponential Waveform, T_C = 110°C)	dv/dt	-	25	-	V/μs
Critical Rate of Rise of Commutation Voltage, (V_D = Rated V_{DRM} , I_{TM} = 11.3 A, Commutating di/dt = 4.1 A/ms, Gate Unenergized, T_C = 80°C)	dv/dt(c)	-	5.0	-	V/μs

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current

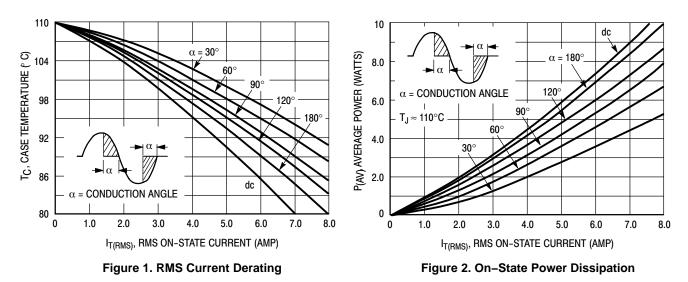


Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.



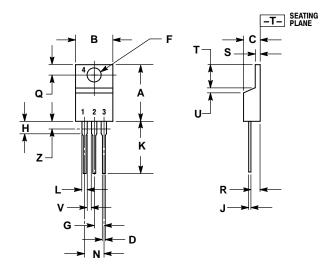
ORDERING INFORMATION

Device	Package	Shipping [†]
MAC228A4	TO-220	50 Units / Rail
MAC228A4G	TO-220 (Pb-Free)	50 Units / Rail
MAC228A6	TO-220	50 Units / Rail
MAC228A6G	TO-220 (Pb-Free)	50 Units / Rail
MAC228A6T	TO-220	50 Units / Rail
MAC228A6TG	TO-220 (Pb-Free)	50 Units / Rail
MAC228A8	TO-220	50 Units / Rail
MAC228A8G	TO-220 (Pb-Free)	50 Units / Rail
MAC228A8T	TO-220	50 Units / Rail
MAC228A8TG	TO-220 (Pb-Free)	50 Units / Rail
MAC228A10	TO-220	50 Units / Rail
MAC228A10G	TO-220 (Pb-Free)	50 Units / Rail

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TO-220 PLASTIC CASE 221A-09 **ISSUE AA**



NOTES: DIMENSIONING AND TOLERANCING PER ANSI 1.

Y14.5M. 1982.

CONTROLLING DIMENSION: INCH.

DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE 3 ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
Ĺ	0.018	0.025	0.46	0.64
Κ	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
Ν	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
C	0.000	0.050	0.00	1.27
۷	0.045		1.15	
Ζ		0.080		2.04

STYLE 4: PIN 1. MAIN TERMINAL 1

MAIN TERMINAL 2 2.

GATE 3.

MAIN TERMINAL 2

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PUBLICATION ORDERING INFORMATION

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Japan: ON Semiconductor, Japan Customer Focus Center 2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051 Phone: 81-3-5773-3850

ON Semiconductor Website: http://onsemi.com

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